Supporting Information

Theoretical study of p-n homojunction SiGe field-effect transistor *via* covalent functionalization

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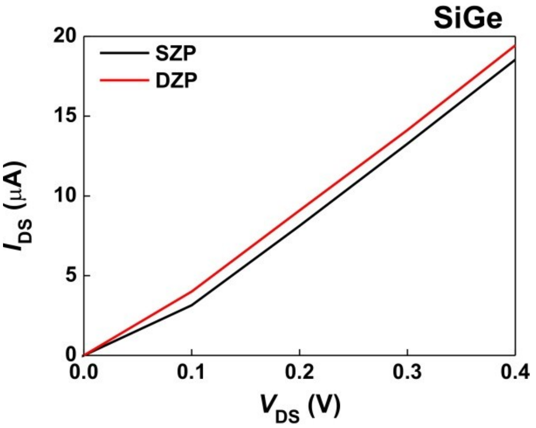

Figure S1. Output characteristic of pristine SiGe FET at V_G = 0 V with single-ζ-polarized (SZP) and double-ζ-polarized (DZP) basis sets, respectively.